

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

SHINTANI et al.

Application No. Unassigned

Art Unit: Unassigned

Filed: August 22, 2001

Examiner: Unassigned

For: METHOD OF
FABRICATING
SEMICONDUCTOR
DEVICE AND WAFER
TREATMENT
APPARATUS
EMPLOYED THEREFOR
AS WELL AS
SEMICONDUCTOR
DEVICE

PRELIMINARY AMENDMENT

Commissioner for Patents
Washington, D. C. 20231

Dear Sir:

Prior to the examination of the above-identified patent application, please enter the following amendments and consider the following remarks.

IN THE SPECIFICATION:

Replace the paragraph beginning at page 1, line 15, with:

High performance is required particularly in a transistor employed for a logic circuit or a system LSI (large-scale integrated circuit) among semiconductor devices. In order to satisfy this requirement, the thickness of a gate insulation film of the transistor is set to not more than 3 nm. Further, a development has recently been made for reducing the thickness of the gate insulating film below 2 nm.